

2SC3180N

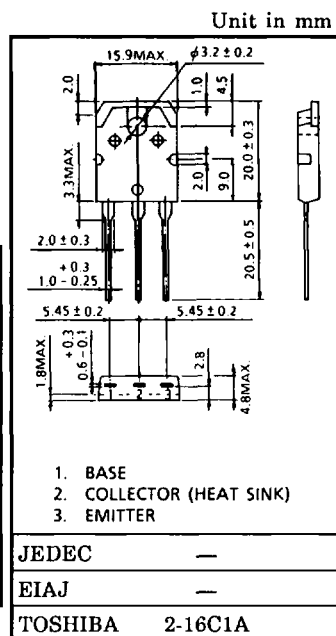
SILICON NPN TRIPLE DIFFUSED TYPE

POWER AMPLIFIER APPLICATIONS.

- Complementary to 2SA1263N
- Recommend for 40W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	6	A
Base Current	I_B	0.6	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)	P_C	60	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{slg}	$-55 \sim 150$	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Weight : 4.7g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 80\text{V}, I_E = 0$	—	—	5.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$	—	—	5.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50\text{mA}, I_B = 0$	80	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	55	—	160	
	$h_{FE(2)}$	$V_{CE} = 5\text{V}, I_C = 3\text{A}$	35	75	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 5\text{A}, I_B = 0.5\text{A}$	—	0.45	2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5\text{V}, I_C = 3\text{A}$	—	0.92	1.5	V
Transition Frequency	f_T	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	—	30	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	—	105	—	pF

Note : $h_{FE(1)}$ Classification R : 55~110, O : 80~160

